



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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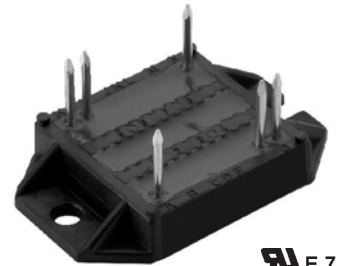
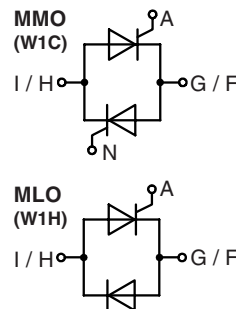


AC Controller Modules

$I_{RMS} = 112 A$
 $V_{RRM} = 800-1400 V$

Preliminary Data

V_{RSM} V_{DSM} V	V_{RRM} V_{DRM} V	Type	
800	800	MMO 110-08io7	MLO 110-08io7
1200	1200	MMO 110-12io7	MLO 110-12io7
1400	1400	MMO 110-14io7	MLO 110-14io7



RU E 72873

Symbol	Conditions	Maximum Ratings	
I_{RMS}	$T_C = 85^\circ C$, 50 - 400 Hz, module	112	A
I_{TRMS}		81	A
I_{TAVM}	$T_C = 85^\circ C$; (180° sine)	51	A
I_{TSM}	$T_{VJ} = 45^\circ C$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	1000 A 1070 A
	$T_{VJ} = 125^\circ C$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	870 A 930 A
I^2t	$T_{VJ} = 45^\circ C$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	5000 A ² s 4810 A ² s
	$T_{VJ} = 125^\circ C$ $V_R = 0$	t = 10 ms (50 Hz), sine t = 8.3 ms (60 Hz), sine	3780 A ² s 3630 A ² s
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ C$ f = 50 Hz, $t_p = 200 \mu s$ $V_D = \frac{2}{3} V_{DRM}$ $I_G = 0.45 A$ $di_G/dt = 0.45 A/\mu s$	repetitive, $I_T = 50 A$ non repetitive, $I_T = I_{TAVM}$	100 A/ μs 500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = 125^\circ C$; $V_{DR} = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)		1000 V/ μs
P_{GM}	$T_{VJ} = 125^\circ C$	$t_p = 30 \mu s$ $t_p = 300 \mu s$	10 W 5 W
	$I_T = I_{TAVM}$		
P_{GAVM}			0.5 W
V_{RGM}			10 V
T_{VJ}			-40...+150 °C
T_{VJM}			150 °C
T_{stg}			-40...+125 °C
V_{ISOL}	50/60 Hz, RMS	t = 1 min	2500 V~
	$I_{ISOL} \leq 1 mA$	t = 1 s	3000 V~
M_d	Mounting torque (M4)		1.5...2.0/14...18 Nm/lb.in.
Weight	typ.		18 g

Features

- Thyristor controller for AC (circuit W1C acc. to IEC) for mains frequency
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Lead suitable for PC board solering

Applications

- Switching and control of single and three phase AC circuits
- Light and temperature control
- Softstart AC motor controller
- Solid state switches

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling
- High power density
- Small and light weight

Data according to IEC 60747 and to a single thyristor/diode unless otherwise stated.

IXYS reserve the right to change limits, conditions and dimensions.

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Symbol	Conditions	Characteristic Values	
I_D, I_R	$T_{VJ} = 125^\circ\text{C}; V_R = V_{RRM}; V_D = V_{DRM}$	\leq	5 mA
V_T	$I_T = 150 \text{ A}; T_{VJ} = 25^\circ\text{C}$	\leq	1.57 V
V_{T0}	For power-loss calculations only		0.85 V
r_T			5.6 m Ω
V_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq 1.5 V \leq 1.9 V
I_{GT}	$V_D = 6 \text{ V}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = -40^\circ\text{C}$	\leq 100 mA \leq 200 mA
V_{GD}	$T_{VJ} = 125^\circ\text{C}; V_D = \frac{2}{3} V_{DRM}$	\leq	0.2 V
I_{GD}		\leq	1 mA
I_L	$T_{VJ} = 25^\circ\text{C}; t_p = 10 \mu\text{s}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	200 mA
I_H	$T_{VJ} = 25^\circ\text{C}; V_D = 6 \text{ V}; R_{GK} = \infty$	\leq	100 mA
t_{gd}	$T_{VJ} = 25^\circ\text{C}; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.45 \text{ A}; di_G/dt = 0.45 \text{ A}/\mu\text{s}$	\leq	2 μs
R_{thJC}	per thyristor; DC		0.8 K/W
	per module		0.4 K/W
R_{thCH}	per thyristor; sine 180° el	typ.	0.12 K/W
	per module	typ.	0.06 K/W
d_s	Creeping distance on surface		11.2 mm
d_A	Creepage distance in air		17.0 mm
a	Max. allowable acceleration		50 m/s ²

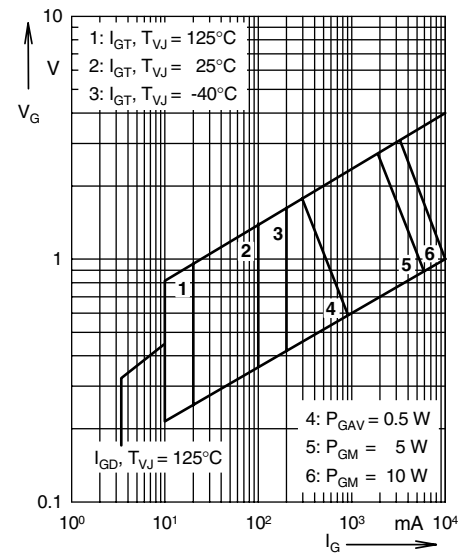
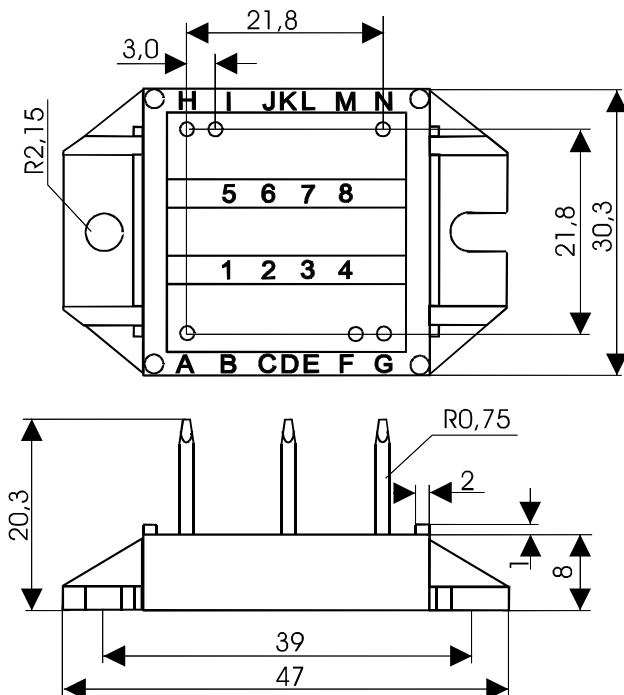
Dimensions in mm (1 mm = 0.0394")


Fig. 1 Gate trigger characteristics

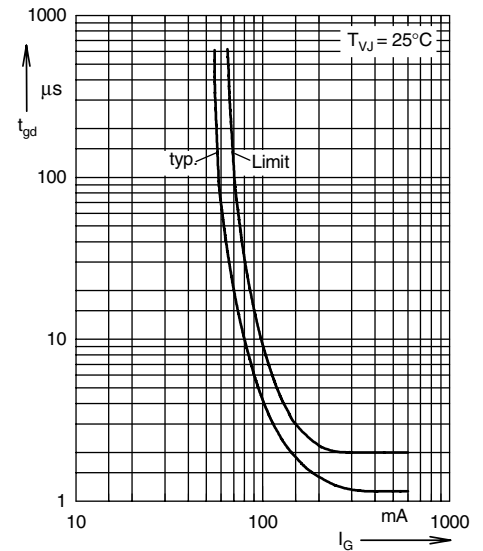


Fig. 2 Gate trigger delay time